REMARKS

Applicant has carefully reviewed and considered the Office Action mailed on May 22, 2002, and the references cited therewith.

Claims 1, 8,15,19, 26, 30, 37, 42, 45, and 49 are amended, no claims are canceled, and no claims are added; as a result, claims 1-54 remain pending in this application.

§112 Rejection of the Claims

Claims 43 and 44 were rejected under 35 USC § 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which Applicant regards as the invention.

Applicant has amended the dependency of claim 43 as suggested by the Examiner. Withdrawal of the 35 USC § 112, second paragraph is respectfully requested.

§102 Rejection of the Claims

Claims 1-54 were rejected under 35 USC § 102(b) as being anticipated by Tanoi (U.S. Patent No. 5,708,621). The rejection states that "in one embodiment in figure 16, Tanoi shows a strapping line of lower resistance than the wordlines bypassing a portion of the wordline."

In discussing Figure 16, Tanoi appers to "divide each high resistance line into two physically and electrically distinct segments" (col. 9, lines 29-30). Tanoi appears to show in Figure 16 a first high-resistance line segment 110 and a second high-resistance line segment 114. Tanoi also appears to show a low resistance line 108 that is coupled individually to both the first high-resistance line segment 110 and the second high-resistance line segment 114 by single interconnecting plugs. However, Tanoi does not show a number of wordlines with a strapping line of lower resistance than the wordlines coupled to a single wordline wherein the strapping line bypasses a portion of the single wordline, and wherein the strapping line is spaced apart from adjacent conductive structures by a distance greater than a wordline pitch; and **at least two channels connecting the strapping line to a first and second end of the portion of the single wordline**. Tanoi also does not appear to show multiple strapping lines attached to a single wordline.

In contrast, Aplicant's claim 1 includes a number of wordlines with a strapping line of lower resistance than the wordlines coupled to a single wordline wherein the strapping line bypasses a portion of the single wordline, and wherein the strapping line is spaced apart from adjacent conductive structures by a distance greater than a wordline pitch; and at least two channels connecting the strapping line to a first and second end of the portion of the single wordline.

Applicant also respectfully submits that in contrast to Tanoi, claim 5 as originally submitted includes a **plurality of strapping lines** of lower resistance than the wordlines coupled to at least one of the number of wordlines **wherein the strapping lines bypass a plurality of portions of a single wordline**, and a plurality of channels connecting the plurality of strapping layers to the wordline.

Further, in contrast to Tanoi, Applicant's claim 8 includes a strapping line of lower resistance than the wordlines, wherein the strapping lines are each located a distance from each other that is greater than the pitch, and at least two channels connecting each strapping line to a portion of a single wordline.

Further, in contrast to Tanoi, Applicant's claim 15 includes a strapping line of lower resistance than the wordlines coupled to a single wordline wherein the strapping line bypasses a portion of the single wordline, and wherein the strapping line is spaced apart from adjacent conductive structures by a distance greater than a wordline pitch, and at least two channels connecting the strapping line to a first and second end of the portion of the single wordline.

Further, in contrast to Tanoi, Applicant's claim 19 includes a number of strapping devices which bypass a portion of single wordlines in the array of parallel wordlines, each strapping device comprising a strapping line of lower resistance than the wordlines, wherein the strapping lines are each located a distance from each other that is greater than the pitch, and at least two channels connecting the strapping line to the single wordline.

Further, in contrast to Tanoi, Applicant's claim 26 includes a strapping line of lower resistance than the wordlines coupled to a single wordline wherein the strapping line bypasses a portion of the single wordline, and wherein the strapping line is spaced apart from adjacent conductive structures by a distance greater than a wordline pitch, and at least two channels

connecting the strapping line to the single wordline.

Further, in contrast to Tanoi, Applicant's claim 30 includes a strapping line of lower resistance than the wordlines, wherein the strapping lines are each located a distance from each other that is greater than the pitch, and at least two channels connecting each strapping line to single wordlines. F.16

Further, in contrast to Tanoi, Applicant's claim 37 includes spacing a number of strapping devices over wordlines in a memory array apart from adjacent strapping devices by a distance greater than a wordline pitch, and connecting individual strapping devices to portions of single wordlines using at least two channels for each strapping device. F.7

Further, in contrast to Tanoi, Applicant's claim 42 includes activating a second wordline in a second memory array, wherein a signal used for activating the second wordline bypasses the first wordline through a strapping device of lower resistance than the first wordline, wherein the strapping device is spaced apart from adjacent strapping devices by a spacing greater than a wordline pitch, and wherein the strapping device is connected to the coupled wordlines by at least two channels. F.16

Further, in contrast to Tanoi, Applicant's claim 45 includes attaching a strapping line of lower resistance than the wordlines to a single wordline wherein the strapping line bypasses a portion of the single wordline, wherein the strapping line is spaced apart from adjacent conductive structures by a spacing greater than a wordline pitch, and connecting the strapping line to the single wordline by forming at least two channels from the strapping line to the single wordline. F.16

Further, in contrast to Tanoi, Applicant's claim 49 includes attaching a number of strapping lines of lower resistance than the wordlines which bypass portions of the wordlines in the array of parallel wordlines, wherein the strapping lines are each located a distance from each other that is greater than the pitch, and connecting the strapping lines to the wordlines by forming at least two channels from each strapping line to individual wordlines. F.7

Because the Tanoi reference does not show every element of Applicant's independent claims, a 35 USC § 102(b) rejection is not supported. Reconsideration and withdrawal of the rejection is respectfully requested with respect to Applicant's independent claims 1, 5, 8,15,19,

26, 30, 37, 42, 45, and 49. Additionally, reconsideration and withdrawal of the rejection is respectfully requested with respect to the remaining claims that depend therefrom as depending on allowable base claims.

CONCLUSION

Applicant respectfully submits that the claims are in condition for allowance and notification to that effect is earnestly requested. The Examiner is invited to telephone Applicant's attorney at (612) 373-6944 to facilitate prosecution of this application.

If necessary, please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

Respectfully submitted,

HUY THANH VO

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938
Minneapolis, MN 55402
(612) 373-6944

Date 8-21-02 By _____
David C. Peterson
Reg. No. 47,857

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner of Patents, Washington, D.C. 20231, on this 21 day of August, 2002.

Tina Kohout _____
Name Signature